

Nell Semiconductors

## Standard Diodes, 350 A (MAGN-A-PAK Power Modules)



MAGN A-PAK

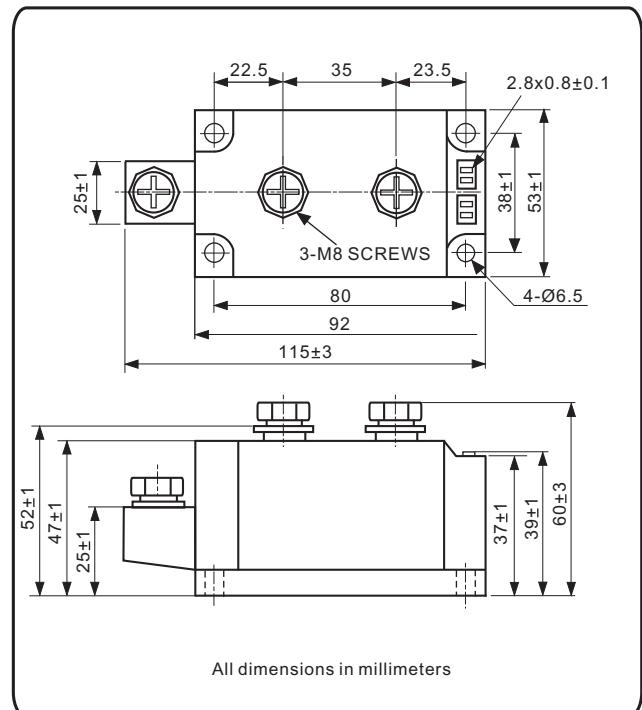


### FEATURES

- UL approved file E320098 
- High current capability
- High surge capability
- High voltage ratings up to 2000 V
- 3000 V<sub>RMS</sub> isolating voltage with non-toxic substrate
- Industrial standard package
- Compliant to RoHS

### APPLICATIONS

- Rectifying bridge for large motor drives
- Rectifying bridge for large UPS
- Rectifying power supplier
- Frequency converters



PRODUCT SUMMARY	
I <sub>F(AV)</sub>	350A
Type	Modules-Diode, High Voltage

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNIT
I <sub>F(AV)</sub>		350	A
	T <sub>C</sub>	100	°C
I <sub>F(RMS)</sub>		550	A
		100	°C
I <sub>FSM</sub>	50 HZ	15000	A
	60 HZ	15705	
I <sup>2</sup> t	50 HZ	1125	kA <sup>2</sup> s
	60 HZ	934	
I <sup>2</sup> √t		11250	kA <sup>2</sup> √s
V <sub>RRM</sub>	Range	800 to 2000	V
T <sub>Stg, T<sub>J</sub></sub>		-40 to 150	°C

## ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> MAXIMUM mA
NKD350 NKJ350 NKC350	08	800	900	20
	12	1200	1300	
	16	1600	1700	
	20	2000	2100	

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNIT
Maximum average forward current at case temperature	I <sub>F(AV)</sub>	180° conduction, half sine wave			350	A
				100	°C	
Maximum RMS forward current	I <sub>F(RMS)</sub>	180° conduction, half sine wave at T <sub>C</sub> = 100°C			550	A
Maximum peak, one-cycle forward non-repetitive surge current	I <sub>FSM</sub>	t = 10ms	No voltage reapplied	Sine half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	15	kA
		t = 8.3ms			15.7	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	t = 10ms	100%V <sub>RRM</sub> reapplied	Sine half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	1125	kA <sup>2</sup> s
		t = 8.3ms			934	
		t = 10ms			790	
		t = 8.3ms			660	
		I <sup>2</sup> √t			11250	kA <sup>2</sup> √s
Maximum forward voltage drop	V <sub>FM</sub>	I <sub>pk</sub> = 1050A, T <sub>J</sub> = 25°C			1.4	V

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNIT
RMS insulation Voltage	V <sub>INS</sub>	t = 1s		3000	V
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>RRM</sub> applied		20	mA
		T <sub>J</sub> = 25°C		20	μA

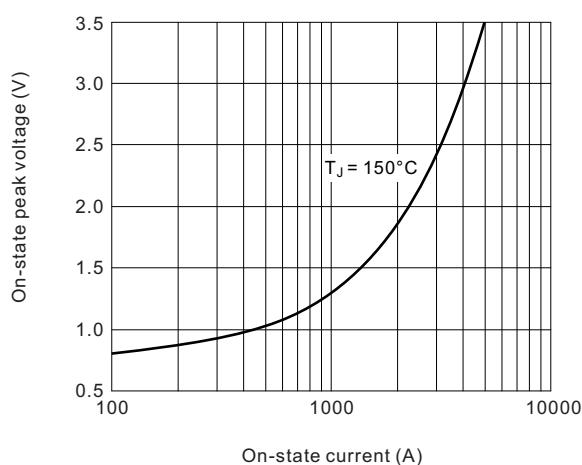
THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNIT
Maximum junction operating and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>				-40 to 150	°C
Maximum thermal resistance, junction to case per junction	R <sub>thJC</sub>	DC operation			0.12	°C/W
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased			0.044	
Mounting torque, ±10% MAP to heatsink, M6 busbar to MAP, M8		A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.			4	N·m
				12		
Approximate weight					900	g
Case style		See dimensions - link at the end of datasheet			MAGN-A-PAK	

## Ordering Information Table

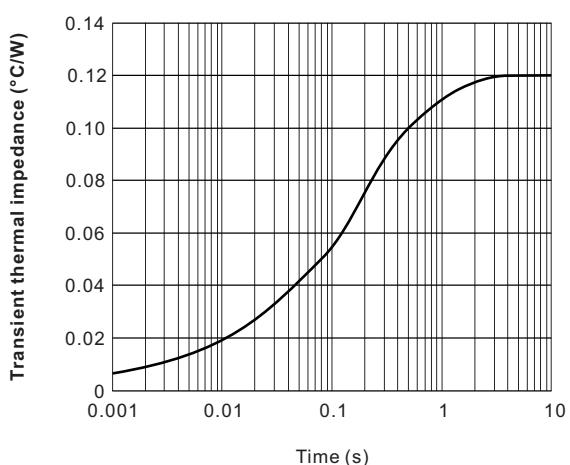
Device code	<b>NKD</b>	<b>350</b>	<b>/</b>	<b>16</b>
	(1)	(2)		(3)

- [1] - Module type, NKD, NKJ and NKC for ( Diode + Diode ) module
- [2] - Current rating :  $I_{F(AV)}$
- [3] - Voltage code x 100 =  $V_{RRM}$

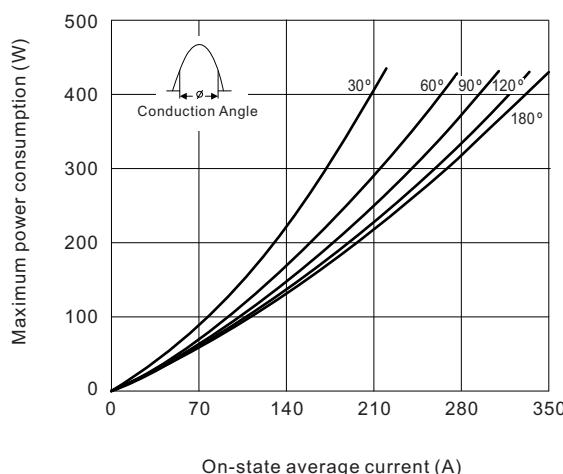
**Fig.1 On-state current vs. voltage characteristic**



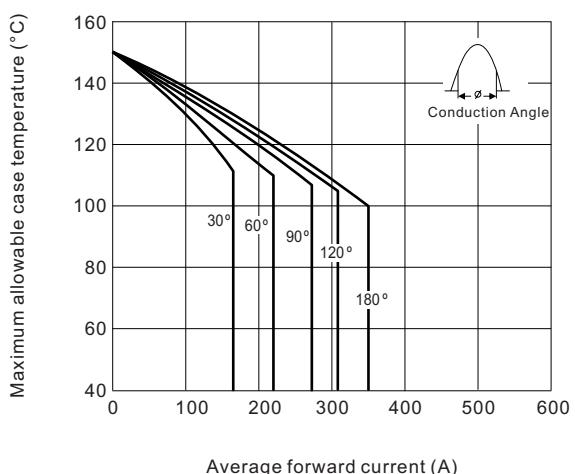
**Fig.2 Transient thermal impedance (junction-case)**

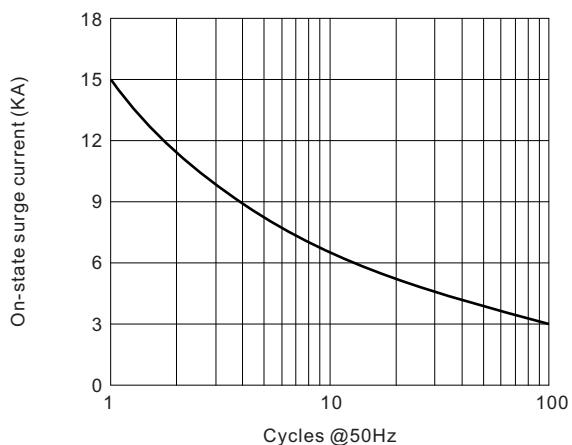


**Fig.3 Power consumption vs. average current**



**Fig.4 Case temperature vs. on-state average current**



**Fig.5 On-state surge current vs cycles****Fig.6  $I^2t$  Characteristic**